

IN THE CLAIMS:

Please amend claims 1, 8, 15, 23, 31, 36, 42 and 48 as follows.

Sub C1
B1
1. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

Sub C3
B2
8. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a pixel electrode formed over said second insulating film.

Sub C3
B3
15. (Amended) A semiconductor device comprising:
a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;

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a gate electrode adjacent to said gate insulating film;
a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

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B3

B4

Subc

23. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film formed on said semiconductor layer;
a gate electrode formed on said gate insulating film;
a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions; and
a transparent pixel electrode formed over said second insulating film.

Subc

B5

31. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;
a gate insulating film adjacent to said semiconductor layer;
a gate electrode adjacent to said gate insulating film;
a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;
a second insulating film comprising an organic resin formed on said first insulating film;
an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure

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including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

Subc 11
B6

30. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;

a gate insulating film adjacent to said semiconductor layer;

a gate electrode adjacent to said gate insulating film;

a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

a second insulating film comprising an organic resin formed on said first insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions.

Subc 13
B7

42. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;

a gate insulating film adjacent to said semiconductor layer;

a gate electrode adjacent to said gate insulating film;

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a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

a second insulating film comprising an organic resin formed on said first insulating film;

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an electrode formed over said second insulating film and connected to one of said first and second impurity regions wherein said electrode has a laminate structure including a first conductive film comprising aluminum and a second conductive film comprising a different material from said first conductive film;

a transparent pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions, wherein said electrode comprises a same material as said conductive layer.

Sub C15
B8
48. (Amended) A semiconductor device comprising:

a semiconductor layer having at least first and second impurity regions and a channel region formed on an insulating surface;

a gate insulating film adjacent to said semiconductor layer;

a gate electrode adjacent to said gate insulating film;

a first insulating film covering at least said gate electrode and said semiconductor layer except for contact holes opened therein;

a second insulating film comprising an organic resin formed on said first insulating film;

an electrode formed over said second insulating film and connected to one of said first and second impurity regions;

a pixel electrode formed over said second insulating film and electrically connected to said one of said first and second impurity regions through said electrode; and

a conductive layer formed over said second insulating film and connected to the other one of said first and second impurity regions,

wherein a portion of said pixel electrode is located below said electrode.